

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE30H14K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

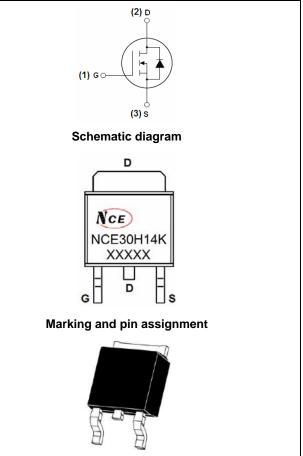
General Features

- V_{DS} =30V,I_D =140A
 - $R_{DS(ON)}$ <3.0m Ω @ V_{GS}=10V
 - $R_{DS(ON)}$ <3.6m Ω @ V_{GS}=4.5V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED! 100% ΔVds TESTED!



TO-252-2L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE30H14K	NCE30H14K	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	30	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	Ι _D	140	А
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	99	A
Pulsed Drain Current	I _{DM}	400	A
Maximum Power Dissipation	PD	130	W
Single pulse avalanche energy (Note 5)	E _{AS}	400	mJ
Operating Junction and Storage Temperature Range	T_J,T_STG	-55 To 175	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	1.25	°C/W	Ì
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Electrical Characteristics (T_A=25 $^\circ\!\!\mathrm{C}$ unless otherwise noted)

	SS SS (th)	V _{GS} =0V I _D =250μA V _{DS} =30V,V _{GS} =0V V _{GS} =±20V,V _{DS} =0V V _{DS} =V _{GS} ,I _D =250μA	30 - -		- 1	V µA
Zero Gate Voltage Drain Current IDS Gate-Body Leakage Current IGS On Characteristics (Note 3) Gate Threshold Voltage VGS VGS Drain-Source On-State Resistance RDS(SS SS (th)	V _{DS} =30V,V _{GS} =0V V _{GS} =±20V,V _{DS} =0V	-	-	1	-
Gate-Body Leakage Current IGS On Characteristics (Note 3) Gate Threshold Voltage VGS Drain-Source On-State Resistance RDS(SS (th)	V _{GS} =±20V,V _{DS} =0V	-	-	-	uА
On Characteristics (Note 3) Gate Threshold Voltage V _{GS} Drain-Source On-State Resistance R _{DS(r)}	(th)		-	-		· · · ·
Gate Threshold Voltage V _{GS} Drain-Source On-State Resistance R _{DS(}		V _{DS} =V _{GS} ,I _D =250µA			±100	nA
Drain-Source On-State Resistance R _{DS(}		V _{DS} =V _{GS} .lp=250µA				
		D0 00,0	1	1.6	2.5	V
		V _{GS} =10V, I _D =20A	-	2.5	3.0	mΩ
	R _{DS(ON)}	V_{GS} =4.5V, I _D =20A	-	2.9	3.6	
Forward Transconductance g _{FS}	s	V_{DS} =5V,I _D =20A	50	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance C _{ls}	s	V _{DS} =15V,V _{GS} =0V,		3780		PF
Output Capacitance Cos	ss	F=1.0MHz		448		PF
Reverse Transfer Capacitance C _{rs}	SS	r = 1.0ivii 12		410		PF
Switching Characteristics (Note 4)						
Turn-on Delay Time t _{d(o}	n)		-	12	-	nS
Turn-on Rise Time t _r		V_{GS} =10V, V_{DS} =15V	-	16	-	nS
Turn-Off Delay Time t _{d(o}	ff)	R _L =0.75Ω,R _{GEN} =3Ω	-	42	-	nS
Turn-Off Fall Time t _f			-	12	-	nS
Total Gate Charge Qg	g			80		nC
Gate-Source Charge Qg	ls	V _{GS} =10V,V _{DS} =15V,I _D =20A		12.4		nC
Gate-Drain Charge Qg	Jd			18.3		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3) Vs	D	V _{GS} =0V,I _S =20A	-	-	1.2	V
Diode Forward Current (Note 2)	;	-		-	140	А
Reverse Recovery Time t _{rr}	r	TJ = 25°C, I _F =20A	-	58	_	nS
Reverse Recovery Charge Qr	r	di/dt = 100A/µs ^(Note3)	-	115	-	nC
Forward Turn-On Time t _{or}		Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD				vIS+ID)

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

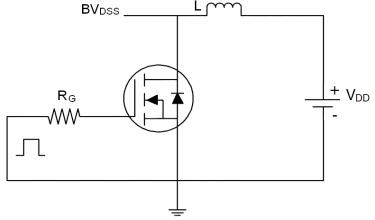
4. Guaranteed by design, not subject to production

5. EAS condition: Tj=25 $^\circ C$,V_DD=15V,V_G=10V,L=0.5mH,Rg=25 Ω

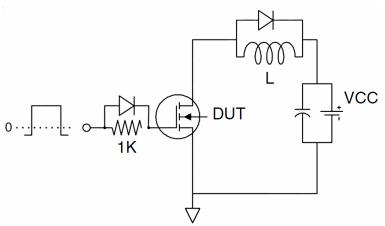


Test circuit

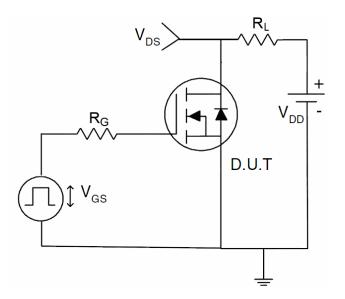
1) E_{AS} test Circuits



2) Gate charge test Circuit:

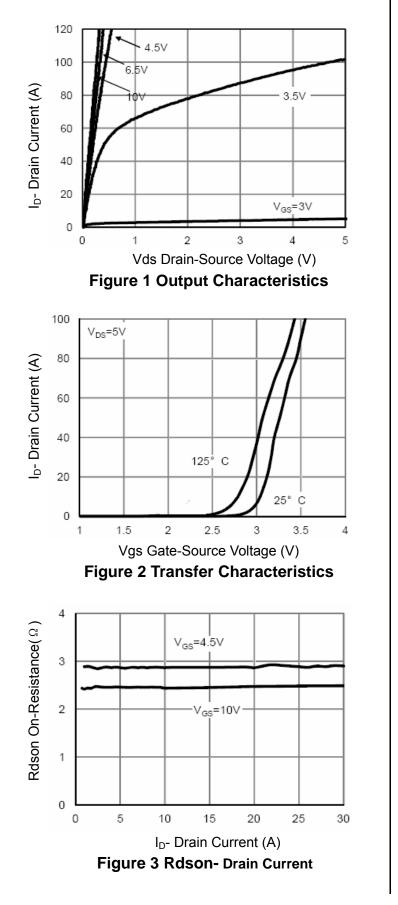


3) Switch Time Test Circuit:





Typical Electrical and Thermal Characteristics (Curves)



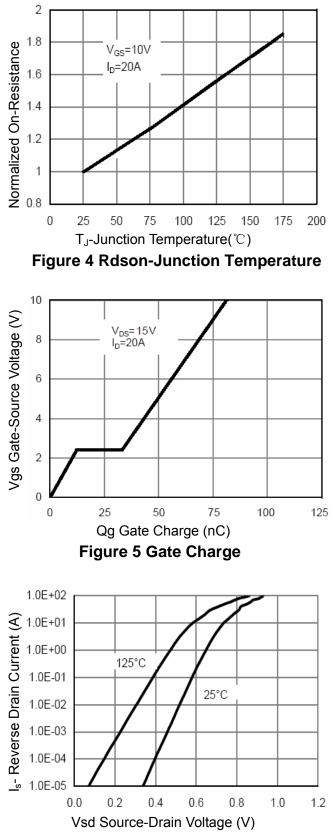
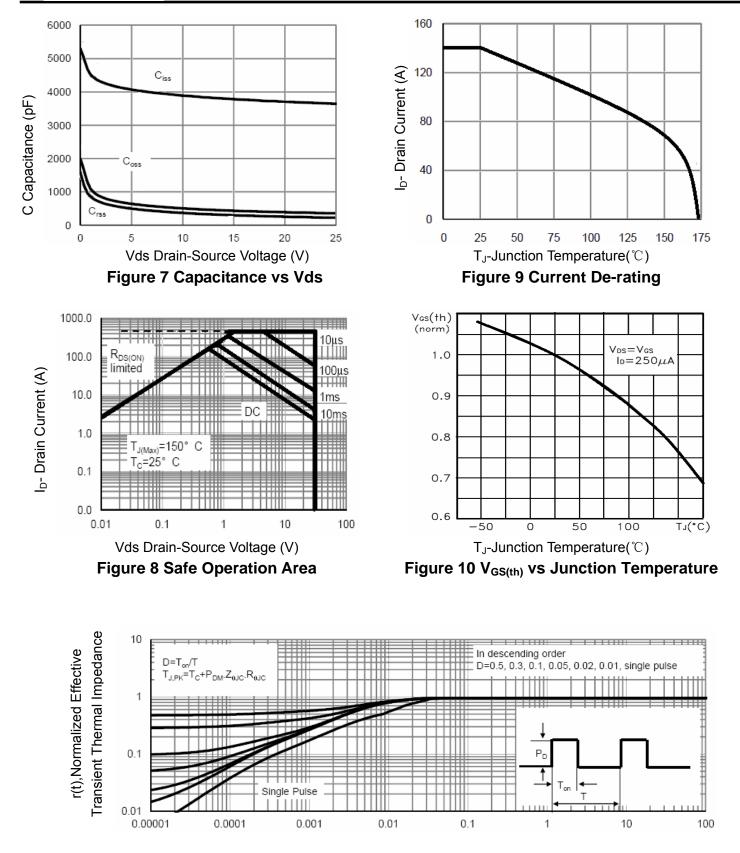


Figure 6 Source- Drain Diode Forward



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NCE30H14K

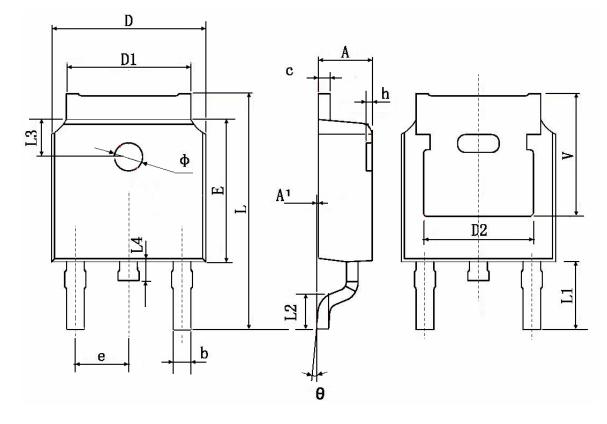


Square Wave Pluse Duration(sec) Figure 11 Normalized Maximum Transient Thermal Impedance



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TO-252 Package Information



Cumple of	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.83	TYP.	0.190 TYP.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900	TYP.	0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600	TYP.	0.063	B TYP.	
L4	0.600	1.000	0.024	0.039	
Φ	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350) TYP.	0.211 TYP.		



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